

- Designed for Complementary Use with the TIP29 Series
- 30 W at 25°C Case Temperature
- 1 A Continuous Collector Current
- 3 A Peak Collector Current
- Customer-Specified Selections Available

TO-220 PACKAGE

Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT
	TIP30		-80	
Collector-base voltage (I _E = 0)	TIP30A	V	-100	v
	TIP30B	V _{CBO}	-120	٧
	TIP30C		-140	
	TIP30		-40	
Collector-emitter voltage (I _B = 0)	TIP30A	V	-60	V
	TIP30B	V _{CEO}	-80	
	TIP30C		-100	
Emitter-base voltage	V _{EBO}	-5	V	
Continuous collector current			-1	Α
Peak collector current (see Note 1)			-3	Α
Continuous base current			-0.4	Α
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)			30	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)			2	W
Unclamped inductive load energy (see Note 4)			32	mJ
Operating junction temperature range			-65 to +150	°C
Storage temperature range			-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds			250	°C

NOTES: 1. This value applies for $t_p \le 0.3$ ms, duty cycle $\le 10\%$.

- 2. Derate linearly to 150°C case temperature at the rate of 0.24 W/°C.
- 3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.
- 4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = -0.4 A, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = -20 V.



electrical characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = -30 mA (see Note 5)	I _B = 0	TIP30 TIP30A TIP30B TIP30C	-40 -60 -80 -100			V
I _{CES}	Collector-emitter cut-off current	$V_{CE} = -80 \text{ V}$ $V_{CE} = -100 \text{ V}$ $V_{CE} = -120 \text{ V}$ $V_{CE} = -140 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	TIP30 TIP30A TIP30B TIP30C			-0.2 -0.2 -0.2 -0.2	mA
I _{CEO}	Collector cut-off current	$V_{CE} = -30 \text{ V}$ $V_{CE} = -60 \text{ V}$	$I_B = 0$ $I_B = 0$	TIP30/30A TIP30B/30C			-0.3 -0.3	mA
I _{EBO}	Emitter cut-off current	V _{EB} = -5 V	I _C = 0				-1	mA
h _{FE}	Forward current transfer ratio	$V_{CE} = -4 V$ $V_{CE} = -4 V$	$I_{\rm C} = -0.2 {\rm A}$ $I_{\rm C} = -1 {\rm A}$	(see Notes 5 and 6)	40 15		75	
V _{CE(sat)}	Collector-emitter saturation voltage	I _B = -125 mA	I _C = -1A	(see Notes 5 and 6)			-0.7	V
V_{BE}	Base-emitter voltage	V _{CE} = -4 V	I _C = -1 A	(see Notes 5 and 6)			-1.3	V
h _{fe}	Small signal forward current transfer ratio	V _{CE} = -10 V	$I_{\rm C} = -0.2 \; {\rm A}$	f = 1 kHz	20			
h _{fe}	Small signal forward current transfer ratio	V _{CE} = -10 V	I _C = -0.2 A	f = 1 MHz	3			

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \ \mu s$, duty cycle $\leq 2\%$.

thermal characteristics

PARAMETER			TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			4.17	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			62.5	°C/W

resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t _{on}	Turn-on time	I _C = -1 A	$I_{B(on)} = -0.1 A$	$I_{B(off)} = 0.1 A$		0.3		μs
t _{off}	Turn-off time	$V_{BE(off)} = 4.3 V$	$R_L = 30 \Omega$	$t_p = 20 \ \mu s, \ dc \le 2\%$		1		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

^{6.} These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

TYPICAL CHARACTERISTICS

Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE

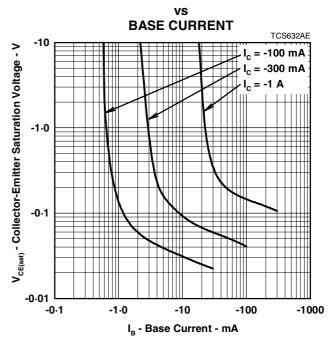
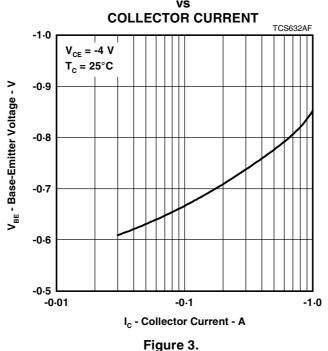


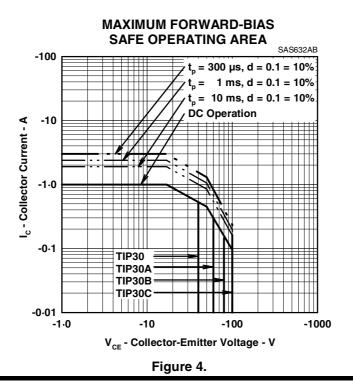
Figure 2.

BASE-EMITTER VOLTAGE



PRODUCT INFORMATION

MAXIMUM SAFE OPERATING REGIONS



THERMAL INFORMATION

MAXIMUM POWER DISSIPATION

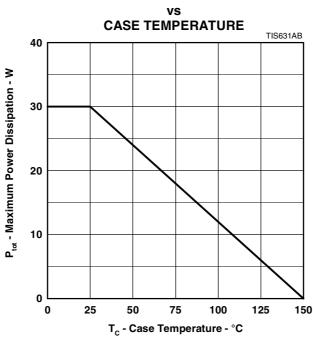


Figure 5.

PRODUCT INFORMATION